

Long wave dynamics in heterogeneous environments

Panayiotis-Yiannis Vrionis The Cyprus Institute

5 July 2023

- Precursor film models (PFM)
- PFM with environmental heterogeneities
- Implementing the PFM solver in Basilisk
- Numerical applications
 - Strong scaling plots
 - Validations cases
 - Examples under heterogeneous effects
- Electrowetting



Based on the long-wave approximation. PFMs avoid the contact line singularity by introducing an utlra-thin film ahead of the moving contact line.

Ideally the precursor film $arepsilon \ll 1$. The smaller, the stiffer the equation becomes.



Based on the long-wave approximation. PFMs avoid the contact line singularity by introducing an utlra-thin film ahead of the moving contact line.

Ideally the precursor film $arepsilon \ll 1$. The smaller, the stiffer the equation becomes.



Main assumptions: Thin flow, negligible inertia, small contact angles. Advantages compared to DNS: Computational cost (dimension reduction), single equation, valid in small contact angles, easier to include additional effects.



How are droplet dynamics affected by the presence of:

- 1. Topographical defects
- 2. Substrate chemical heterogeneities
- 3. Body-forces
- 4. Thermal effects
- 5. Electric fields*



Case of multiple droplets moving on an inclined, chemically heterogeneous substrate. AMR. 67 K < nc < 220 K

Aim: Development of a PFM solver that incorporates these heterogeneities and can deal with isolated and multiple droplets.



The governing equation for the film height is written as $h(\mathbf{x}, t)$

$$\partial_t h + \boldsymbol{\nabla} \cdot \mathbf{F}(h, \boldsymbol{\nabla} h, \Delta h) = 0$$

$$\mathbf{F} = h^3 \left[\mathbf{\nabla} \underline{\Delta}(h) - \mathbf{\nabla} \underbrace{\Pi}(h) \right]_{\text{disjoining}}$$

The governing equation for the film height is written as $h(\mathbf{x}, t)$

$$\partial_t h + \boldsymbol{\nabla} \cdot \mathbf{F}(h, \boldsymbol{\nabla} h, \Delta h) = 0$$

with

$$\mathbf{F} = h^3 \left[\nabla \underbrace{\Delta(h+s)}_{\text{curvature}} - \nabla \underbrace{\Pi(h)}_{\text{disjoining}} \right]$$

• Substrate Roughness



The governing equation for the film height is written as $h(\mathbf{x}, t)$

$$\partial_t h + \boldsymbol{\nabla} \cdot \mathbf{F}(h, \boldsymbol{\nabla} h, \Delta h) = 0$$

$$\mathbf{F} = h^{3} \left[\nabla \underbrace{\Delta(h+s)}_{\text{curvature}} - \nabla \underbrace{\Pi(h,x)}_{\text{disjoining}} \right]$$

- Substrate Roughness
- Substrate Chemical Heterogeneity



The governing equation for the film height is written as $h(\mathbf{x}, t)$

$$\partial_t h + \boldsymbol{\nabla} \cdot \mathbf{F}(h, \boldsymbol{\nabla} h, \Delta h) = 0$$

$$\mathbf{F} = h^3 \left[\nabla \underbrace{\Delta(h+s)}_{\text{curvature}} - \nabla \underbrace{\Pi(h,x)}_{\text{disjoining}} - w_1 \nabla(h+s) + w_2 \mathbf{e}_1 \right]$$

- Substrate Roughness
- Substrate Chemical Heterogeneity
- Body Forces (gravity and/or external forces)



The governing equation for the film height is written as $h(\mathbf{x}, t)$

 $\partial_t h + \nabla \cdot \mathbf{F}(h, \nabla h, \Delta h) + S(h, \nabla h, \Delta h) = 0$

$$\mathbf{F} = h^{3} \left[\mathbf{\nabla} \underbrace{\Delta(h+s)}_{\text{curvature}} - \mathbf{\nabla} \underbrace{\Pi(h, x)}_{\text{disjoining}} - w_{1} \mathbf{\nabla}(h+s) + w_{2} \mathbf{e}_{1} \right]$$
$$\mathbf{S} = \mathbf{J} = \frac{\mathcal{E} - \delta(\Delta(h+s) - \mathbf{\nabla}\Pi(h, x) - w_{1} \mathbf{\nabla}(h+s))}{\mathcal{K} + h + s}$$

- Substrate Roughness
- Substrate Chemical Heterogeneity
- Body Forces (gravity and/or external forces)
- Thermal Effects (evaporation/condensation)



Numerical implementation - Discretization

Implicit discretization to ease PDE stiffness Different heterogeneity combinations call for modularity

Discretization

- 2nd order time discretization with variable time-stepping (a-BDF2)
- Newton linearization
- 2nd order space discretization
- Geometric multigrid method





Implicit time discretization

 $\mathcal{R}(h_{n+1}, \hat{h}_{n+1})\delta t_{n+1} + \alpha h_{n+1} = \beta h_n - \gamma h_{n-1},$ δt_{n+1} defined based on number of MG cycles





Implicit time discretization

 $\mathcal{R}(h_{n+1}, \hat{h}_{n+1}) \delta t_{n+1} + \alpha h_{n+1} = \beta h_n - \gamma h_{n-1}, \\ \delta t_{n+1} \text{ defined based on number of MG cycles}$ **Linearization**

Find linearized operator (L) for MG.

$$\partial_t h = - oldsymbol{
abla} \cdot oldsymbol{\mathsf{F}} \approx - oldsymbol{
abla} \cdot oldsymbol{\mathsf{F}} - oldsymbol{
abla} \cdot (\partial_h oldsymbol{\mathsf{F}} \,\delta h)$$
 , $\,\delta h = h - \hat{h}$

Newton iterations until $h_{n+1} \approx \hat{h}_{n+1}$





Implicit time discretization

 $\mathcal{R}(h_{n+1}, \hat{h}_{n+1}) \delta t_{n+1} + \alpha h_{n+1} = \beta h_n - \gamma h_{n-1}, \\ \delta t_{n+1} \text{ defined based on number of MG cycles} \\ \textbf{Linearization}$

Find linearized operator (L) for MG.

$$\partial_t h = - \nabla \cdot \mathbf{F} \approx - \nabla \cdot \mathbf{F} - \nabla \cdot (\partial_h \mathbf{F} \, \delta h)$$
, $\delta h = h - \hat{h}$

Newton iterations until $h_{n+1} \approx \hat{h}_{n+1}$

Basilisk details

FDs for residual and relaxation functions

static double residual_thin(...) { ... }
static void relax_thin(...) { ... }

Conditional compilation for heterogeneities

⊭if ROUGH

addRoughnessContributions(...)





Scalability

Strong scaling plots obtained from simulations of a single droplet (1000 timesteps) on the HPC VEGA using AMD EPYC Rome 7H12 @ 2.6 GHz CPUs.



Adaptive mesh refinement \rightarrow significant communication overhead.

Increasing adaptation intervals or avoiding it for small cell count changes can help.



Comparison of sessile droplet radius expansion rate with (Bo = 1) and without (Bo = 0)gravity effects.

$$r(t=0) = 1, \ h_{max}(t=0) = 4, \ V = 2\pi, \ L0 = 5, \ L = 9, \ \varepsilon = 3 \times 10^{-3}$$





Comparison of droplet contact lines at different simulation times to validate substrate chemical heterogeneity effects between Basilisk and ODE.

Contours refer to the Hamaker coefficient with values; $1 < \mathcal{H}(\mathbf{x}) < 10 = 1$ (white to black).

$$r(t=0) = 1$$
, $V = 2\pi$, $\varepsilon = 3 \times 10^{-3}$





Case of multiple droplets moving on an inclined, chemically heterogeneous substrate.

Small droplets either get absorbed by the much larger ones or coalesce with other small droplets.

Contours refer to 0.08 < h < 0.8values. Low *h* values are excluded for clarity.





Simulation examples - Dropwise condensation

Simulations aiming to qualitatively capture the drop-wise condensation on an inclined substrate.

The area of low Hamaker coefficient, i.e. high hydrophilicity act as droplet inception point

As the droplet increases in size, it de-pinns from the inception point and starts to move downstream.



Hamaker coefficient profile. Blue: 0.1; Red: 1.0





Since the droplet is larger, it is able to condensate on its own increasing in volume and accelerating downstream.

After a critical mass is reached, the **corner** becomes unstable and ejects a drop.^a

The droplets grow until reaching the boundaries. Here $h_{max} \approx 0.4$.





^aPodgorski T et al., (2001), Phys. Rev. Lett., 87, 036102.



Electrowetting - Droplet dynamics under electric fields



In the **thin film limit**, $\nabla^2 \Phi = \partial_{zz} \Phi_i$ leading to closed-form $\Phi_i(z)$ expressions^a,

$$\Phi_1(z) = \Phi_1(t) - z \frac{\Phi_1(t) - (\beta - h)Q}{h(1 - \epsilon) + \epsilon\beta}$$
$$\Phi_2(z) = (\beta - z) \frac{\epsilon \Phi_1(t) + hQ}{h(1 - \epsilon) + \epsilon\beta}$$

Assuming **negligible inertia** and the **leaky** dielectric model^b

$$\partial_{t}h + \nabla \cdot \mathbf{F}^{e}(h, Q) = 0$$

$$\partial_{t}Q + \nabla \cdot \left(\frac{Q}{2h}\mathbf{F}^{e}(h, Q)\right) = \Psi_{c} \left(\partial_{z}\Phi_{2} - \sigma\partial_{z}\Phi_{1}\right)_{z=h}$$

$$\mathbf{F}^{e}(h, Q) = \mathbf{F}(h) \underbrace{-\frac{3h^{2}}{2}E\mathcal{M}^{t} - h^{3}E\mathcal{M}^{n}}_{Maxwell \text{ Stresses}}$$

where Q the interfacial free charge density.

Coupled system of equations of *Q* and *h* is solved by modifying the existing thin film Multigrid solver.

^aKainikkara M, et al., (2021), npj Microgravity, 7,1-47.

^bMelcher JR, Taylor GI, (1969), Annu. Rev. Fluid Mech., 1,111–46

Evaporating droplet on a chemically heterogeneous substrate under the effect of an electric field.

The presence of a time-varying electric field $(\Phi_0 = 12, T_{\Phi} = 5s)$ causes the Maxwell stresses to vary in time, leading to a vibrating droplet.

Simultaneously, the droplet decreases in size due to it evaporating.





Remarks

- Optimal scaling with uniform meshes. Adaptation could be better with some fine-tuning
- Good agreement with ODE data
- Effect of precursor film on condensing case

Challenges/ Future Work

- Pseudo-3D formulations for diffusion-limited evaporation
- Extension to non-rigid substrates



Precursor film solver solution process



B